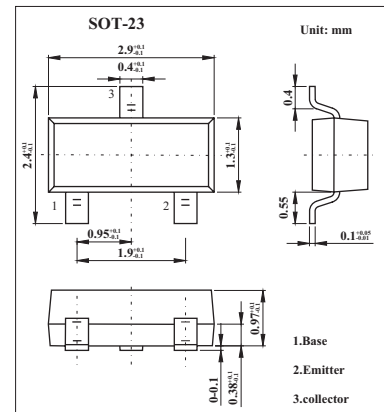


Switching Transistor

FM718

■ Features

- 625mW power dissipation.
- I_C CONT 2.5A.
- I_C up to 10A peak pulse current.
- Excellent h_{fe} characteristics up to 10A (pulsed).
- Extremely low saturation voltage e.g. 10mV typ..
- Exhibits extremely low equivalent on-resistance; $R_{CE(sat)}$.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CM}	-6	A
Collector current	I_C	-1.5	A
Base current	I_B	-500	mA
Power dissipation	P_{tot}	625	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FMMT718

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-20	-65		V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-20	-55		V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5	-8.8		V
Collector cutoff current	ICBO	VCE=-15V			-100	nA
Emitter cut-off current	IEBO	VEB=-4V			-100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=-0.1A, IB=-10mA IC=-1A, IB=-10mA IC=-1.5A, IB=-50mA		-16 -130 -145	-40 -200 -220	mV
Base-emitter saturation voltage *	VBE(sat)	IC=-1.5A, IB=-50mA		-0.87	-1	V
Base-emitter voltage *	VBE(ON)	IC=-2A, VCE=-2V		-0.81	-1	V
DC current gain *	hFE	IC=-10mA, VCE=-2V IC=-0.1A, VCE=-2V IC=-2A, VCE=-2V IC=-4A, VCE=-2V IC=-6A, VCE=-2V	300 300 150 35 15	475 450 230 70 30		
Current-gain-bandwidth product	fT	IC=-50mA, VCE=-10V, f=100MHz	150	180		MHz
Output capacitance	Cobo	VCE=-10V, f=1MHz		21	30	pF
Turn-on time	t(on)	VCC=-10V, IC=-1A		40		ns
Turn-off time	t(off)	IB1=-IB2=-20mA		670		ns

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	718
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